



## PDFN5X6-8L P Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管

### ■ Features 特点

Low on-resistance 低导通电阻

$R_{DS(ON)}=8.5m\Omega(\text{Type})@V_{GS}=-10V$

$R_{DS(ON)}=10m\Omega(\text{Type})@V_{GS}=-4.5V$

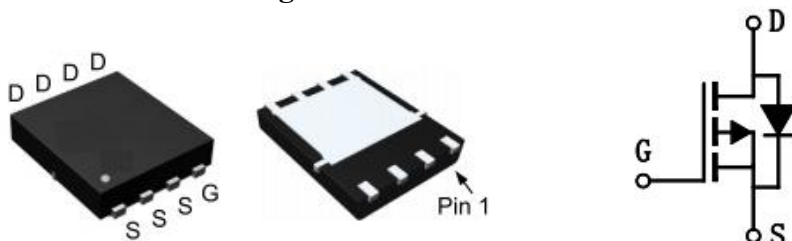
### ■ Applications 应用

Load Switch 负载开关

PWM Application 脉宽调制

Power Management 电源管理

### ■ Internal Schematic Diagram 内部结构



### ■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	$BV_{DSS}$	-40	V
Gate- Source Voltage 栅极-源极电压	$V_{GS}$	$\pm 20$	V
Drain Current (continuous)漏极电流-连续	$I_D$ (at $T_C = 25^\circ\text{C}$ at $T_A = 25^\circ\text{C}$ )	-70 -20	A
Drain Current (pulsed)漏极电流-脉冲	$I_{DM}$	-140	A
Total Device Dissipation 总耗散功率	$P_{TOT}(\text{at } T_C/T_A = 25^\circ\text{C})$	59.5/2.08	W
Avalanche Energy(Single Pulse)雪崩能量	$E_{AS}$	125	mJ
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	60	$^\circ\text{C}/\text{W}$
Junction/Storage Temperature 结温/储存温度	$T_j, T_{stg}$	-55~150	$^\circ\text{C}$



## ■ Electrical Characteristics 电特性

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压( $I_D = -250\mu\text{A}, V_{GS}=0\text{V}$ )	$BV_{DSS}$	-40	—	—	V
Gate Threshold Voltage 栅极开启电压( $I_D = -250\mu\text{A}, V_{GS} = V_{DS}$ )	$V_{GS(th)}$	-1.0	-1.5	-2.5	V
Zero Gate Voltage Drain Current 零栅压漏极电流( $V_{GS}=0\text{V}, V_{DS}= -40\text{V}$ )	$I_{DSS}$	—	—	-1	$\mu\text{A}$
Gate Body Leakage 栅极漏电流( $V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$ )	$I_{GSS}$	—	—	$\pm 100$	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻( $I_D = -20\text{A}, V_{GS} = -10\text{V}$ ) ( $I_D = -10\text{A}, V_{GS} = -4.5\text{V}$ )	$R_{DS(ON)}$	—	8.5 10	13 18	$\text{m}\Omega$
Diode Forward Voltage Drop 内附二极管正向压降( $I_{SD} = -1\text{A}, V_{GS}=0\text{V}$ )	$V_{SD}$	—	-0.7	-1	V
Input Capacitance 输入电容 ( $V_{GS}=0\text{V}, V_{DS} = -20\text{V}, f=1\text{MHz}$ )	$C_{ISS}$	—	3125	—	pF
Common Source Output Capacitance 共源输出电容( $V_{GS}=0\text{V}, V_{DS} = -20\text{V}, f=1\text{MHz}$ )	$C_{OSS}$	—	812	—	pF
Reverse Transfer Capacitance 反馈电容 ( $V_{GS}=0\text{V}, V_{DS} = -20\text{V}, f=1\text{MHz}$ )	$C_{RSS}$	—	575	—	pF
Total Gate Charge 栅极电荷密度 ( $V_{DS} = -20\text{V}, I_D = -20\text{A}, V_{GS} = -10\text{V}$ )	$Q_g$	—	80	—	nC
Gate Source Charge 栅源电荷密度 ( $V_{DS} = -20\text{V}, I_D = -20\text{A}, V_{GS} = -10\text{V}$ )	$Q_{gs}$	—	14	—	nC
Gate Drain Charge 栅漏电荷密度 ( $V_{DS} = -20\text{V}, I_D = -20\text{A}, V_{GS} = -10\text{V}$ )	$Q_{gd}$	—	19	—	nC
Turn-ON Delay Time 开启延迟时间 ( $V_{DS} = -20\text{V}, I_D = -1\text{A}, R_{GEN}=6\Omega, V_{GS} = -10\text{V}$ )	$t_{d(on)}$	—	19	—	ns
Turn-ON Rise Time 开启上升时间 ( $V_{DS} = -20\text{V}, I_D = -1\text{A}, R_{GEN}=6\Omega, V_{GS} = -10\text{V}$ )	$t_r$	—	16	—	ns
Turn-OFF Delay Time 关断延迟时间 ( $V_{DS} = -20\text{V}, I_D = -1\text{A}, R_{GEN}=6\Omega, V_{GS} = -10\text{V}$ )	$t_{d(off)}$	—	115	—	ns
Turn-OFF Fall Time 关断下降时间 ( $V_{DS} = -20\text{V}, I_D = -1\text{A}, R_{GEN}=6\Omega, V_{GS} = -10\text{V}$ )	$t_f$	—	71	—	ns



## ■ Typical Characteristic Curve 典型特性曲线

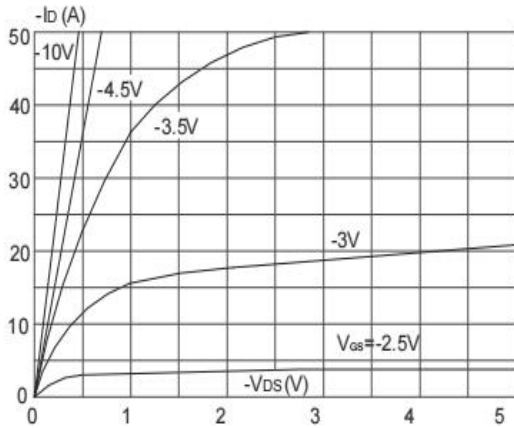


Figure 1: Output Characteristics

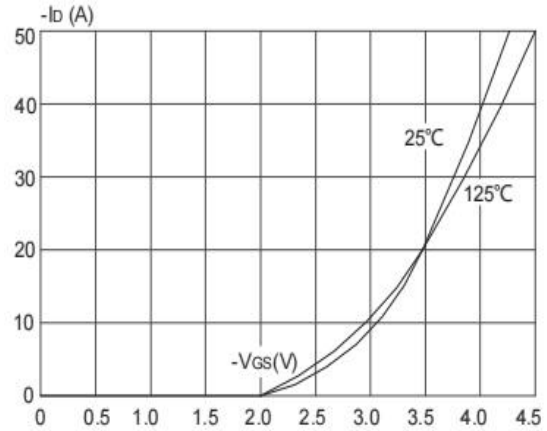


Figure 2: Transfer Characteristics

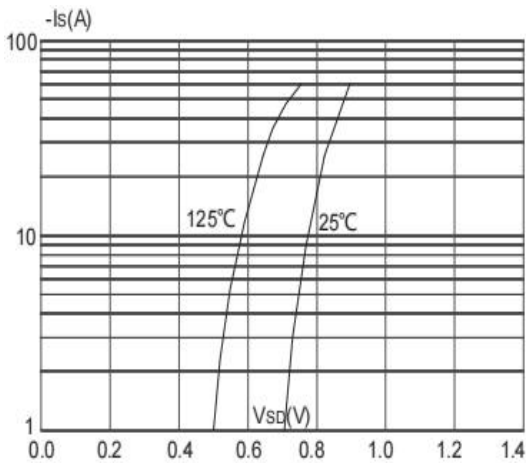


Figure 3: Diode Characteristics

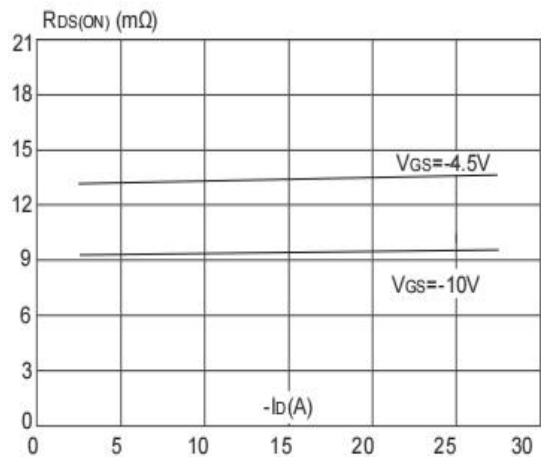


Figure 4: On-Resistance vs. Drain Current

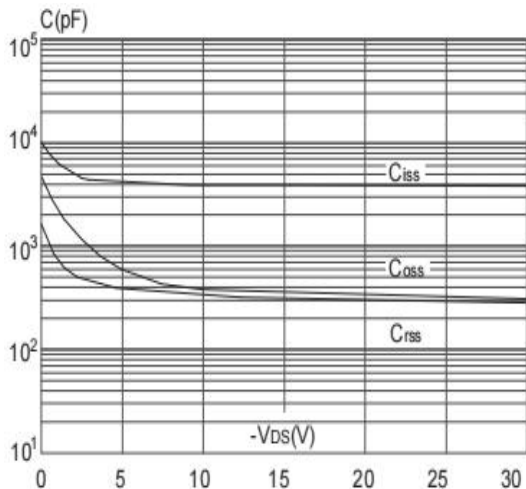


Figure 5: Capacitance Characteristics

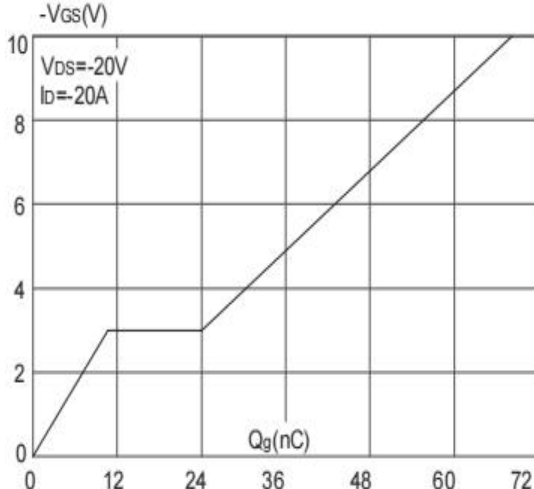


Figure 6: Gate-Charge Characteristics

## ■ Typical Characteristic Curve 典型特性曲线

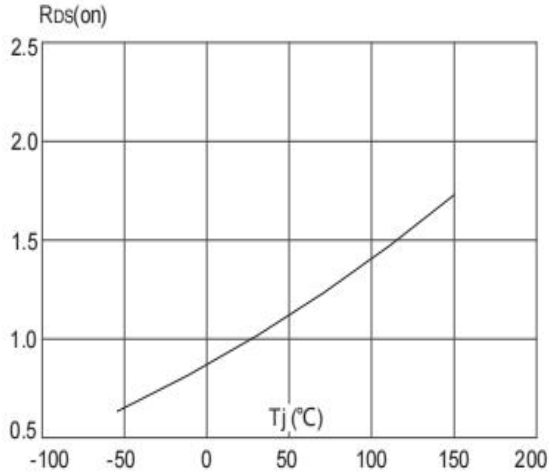


Figure 7: On-Resistance vs. Tj

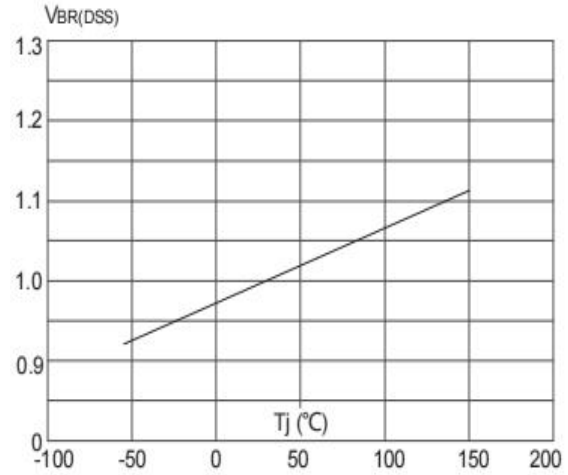


Figure 8: Breakdown Voltage vs. Tj

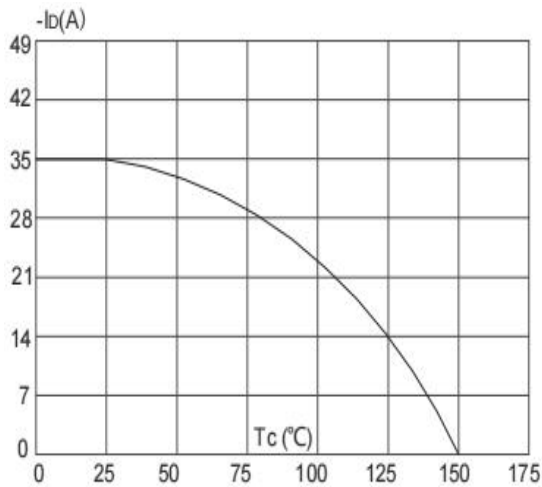


Figure 9: Drain Current Characteristics

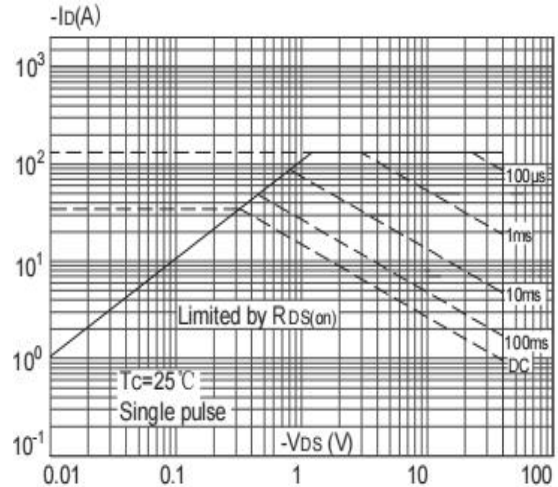


Figure 10: Safe Operating Area

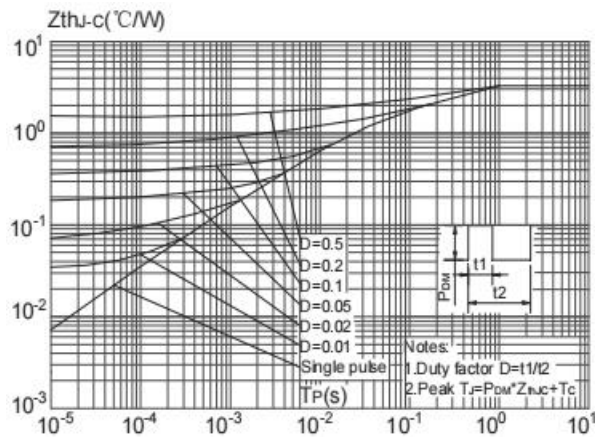


Figure 11: Transient Thermal Response Curve

■ Dimension 外形封装尺寸

